Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

## 2SK2606

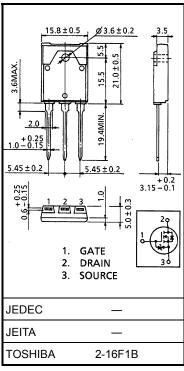
# DC-DC Converter, Relay Drive and Motor Drive Applications

• Low drain-source ON resistance  $: RDS (ON) = 1.0 \Omega (typ.)$ • High forward transfer admittance  $: |Y_{fs}| = 7.0 S (typ.)$ • Low leakage current  $: IDSS = 100 \mu A (max) (VDS = 640 V)$ 

• Enhancement mode  $V_{th} = 2.0 \sim 4.0 \text{ V (Vps} = 10 \text{ V, Ip} = 1 \text{ mA})$ 

#### Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	800	V	
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	800	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	I <sub>D</sub>	8	Α	
	Pulse (Note 1)	$I_{DP}$	24	Α	
Drain power dissipation	n (Tc = 25°C)	$P_{D}$	85	W	
Single pulse avalanche	e energy (Note 2)	E <sub>AS</sub>	883	mJ	
Avalanche current		I <sub>AR</sub>	8	Α	
Repetitive avalanche e	nergy (Note 3)	E <sub>AR</sub>	8.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 5.8 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.47	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	41.6	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 25.0 mH,  $I_{AR}$  = 8 A,  $R_G$  = 25  $\Omega$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



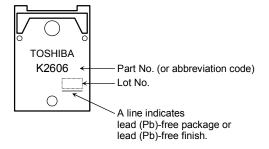
## Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	_	_	±10	μA
Gate-source bro	eakdown voltage	V (BR) GSS	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 640 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	800	_	_	V
Gate threshold v	/oltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A,	_	1.0	1.2	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4 A	3.0	7.0	_	S
Input capacitano	ce	C <sub>iss</sub>			2160	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	45	_	
Output capacitance		C <sub>oss</sub>		_	200	_	
Switching time	Rise time	t <sub>r</sub>	$V_{GS} = \frac{10V}{V_{GS}} = \frac{I_{D} = 4.0A}{V_{Out}} = \frac{V_{Out}}{V_{DD}} = \frac{100\Omega}{V_{DD}}$ $V_{DD} = \frac{100\Omega}{V_{DD}} =$	_	25	_	- ns
	Turn-on time	t <sub>on</sub>		_	60	_	
	Fall time	t <sub>f</sub>		_	25	_	
	Turn-off time	t <sub>off</sub>		_	110	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	68		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$		38	_	nC
Gate-drain ("miller") Charge		$Q_{gd}$		_	30		

### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>		_	_	8	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	24	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V	_	_	-1.9	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V, dI <sub>DR</sub> / dt = 100 A / μs	1	1500		ns
Reverse recovery charge	Q <sub>rr</sub>	1DR - 0 Λ, VGS - 0 V, diDR / dt - 100 A / μs		19	_	μC

### Marking



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